

REMARKS

Claims 12-14 are pending in this application. Claims 1-4 and 7-9 stand withdrawn.

By this Amendment, claims 5, 6, 10 and 11 are canceled. Claims 12-14 are added.

In particular, claim 12 is added to recite the subject matter recited in claims 5, 6 and 11, and to recite additional features disclosed in the specification at, for example, paragraphs [0027] - [0030]. Claim 13 recites subject matter similar to that originally recited in claim 10. Claim 14 depends from claim 12.

Reconsideration of the application is respectfully requested.

The Office Action rejects claims 5, 6 and 10 under 35 U.S.C. §103(a) over Shimoda-I in view of Shimoda-II and U.S. Patent Publication No. 2002/0173120 to Enquist; and rejects claim 11 under 35 U.S.C. §103(a) over Shimoda-I in view of Applicants' admitted prior art (AAPA) and Enquist. These rejections are moot with respect to canceled claims 5, 6, 10 and 11, and are respectfully traversed with regard to claims 12-14, to the extent applicable.

The Office Action recognizes that Shimoda-I and Shimoda-II do not disclose or suggest a transfer that includes electrically connecting a functional element to a wiring line of a second substrate, but asserts that Enquist discloses this feature. However, Enquist does not supply the subject matter lacking in Shimoda-I and Shimoda-II, because Enquist does not disclose or suggest peeling the at least one element chip from the first substrate, by irradiating a laser beam onto the peeling layer, after electrically connecting the at least one element chip and the wiring line, as recited in claim 12.

Enquist discloses connecting the element 41 to the wiring line 47 after the transfer of the element 41 from substrate 40 to substrate 45. See Figs. 11-15 and paragraphs [0078] through [0080]. In particular, Enquist discloses that a via hole 50 is etched after the first substrate 40 has been removed. Then, interconnect 51 is formed in via hole 50 to electrically connect element 41 with wiring line 47. Enquist does not appear to disclose or suggest

connecting the element 41 to the wiring line 47 before a peeling step. Therefore, Enquist does not disclose or suggest peeling the at least one element chip from the first substrate, by irradiating a laser beam onto the peeling layer, after electrically connecting the at least one element chip and the wiring line, as recited in claim 12. Hence, Enquist does not supply the subject matter lacking in Shimoda-I and Shimoda-II. Thus, Shimoda-I, Shimoda-II and Enquist, either individually or in combination, do not disclose or suggest peeling the at least one element chip from the first substrate, by irradiating a laser beam onto the peeling layer, after connecting the at least one element chip and the wiring line, as recited in claim 12.

Furthermore, Shimoda-I, Shimoda-II, Enquist and AAPA, either individually or in combination, do not disclose or suggest " wherein the step of forming the thin film transistor includes the steps of forming an amorphous silicon layer on the peeling layer, crystallizing the amorphous silicon layer by irradiating a laser beam thereonto, and then forming a polycrystalline silicon layer by patterning the crystallized amorphous silicon layer, forming an insulating film on the first substrate and the polycrystalline silicon layer, and forming the gate metal on the insulating film, and then forming a gate electrode by patterning the gate metal," as recited in claim 12.

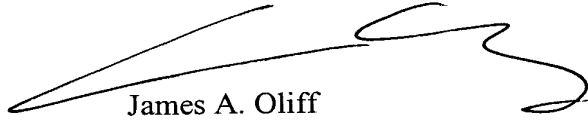
For any or all of the above reasons, the applied references do not disclose or suggest the subject matter recited in claim 12, and claims 13 and 14 depending therefrom.

Accordingly, claims 12-14 are patentable over the applied references.

In view of the foregoing, it is respectfully submitted that this application is in condition for allowance. Favorable reconsideration and prompt allowance of claims 12-14 are earnestly solicited.

Should the Examiner believe that anything further would be desirable in order to place this application in even better condition for allowance, the Examiner is invited to contact the undersigned at the telephone number set forth below.

Respectfully submitted,



James A. Oliff
Registration No. 27,075

Gang Luo
Registration No. 50,559

JAO:GXL/rle

Attachment:
Request for Continued Examination

Date: April 20, 2006

OLIFF & BERRIDGE, PLC
P.O. Box 19928
Alexandria, Virginia 22320
Telephone: (703) 836-6400

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